

Cite this: *Mater. Adv.*, 2024,  
5, 7659

# Enhanced efficiency of dye-sensitized solar cells via controlled thickness of the WO<sub>3</sub> Langmuir–Blodgett blocking layer in the Debye length regime†

Neeraj Kumar,<sup>ad</sup> Sipra Choudhury,<sup>ib</sup>bd Aman Mahajan<sup>id</sup>c and Vibha Saxena<sup>id</sup>\*ad

Generally, a thin (>50 nm) transition metal oxide (TMO) film (such as TiO<sub>2</sub>) is employed as an interfacial layer (also called a blocking layer, BL) between FTO and mesoporous TiO<sub>2</sub> in a dye-sensitized solar cell (DSC). The function of this layer is to provide full coverage of FTO so as to reduce back electron recombination without compromising transparency and charge transport properties. Recent research has demonstrated that WO<sub>3</sub> has better charge transport and stability than TiO<sub>2</sub> and therefore has the potential to be employed as a hole blocking layer. Furthermore, ultra-thin TMO films having thickness less than the Debye length (characteristic length of the space charge layer in the WO<sub>3</sub>,  $L_D$ ) are expected to provide better interfacial and optical properties. However, reducing the thickness in such thin films has been challenging owing to available preparation methods. In this work, the Langmuir–Blodgett (LB) technique has been adopted to prepare high quality crystalline BL of WO<sub>3</sub> of controlled thickness in the range of  $L_D$  (4–20 nm). The interfacial properties such as charge transport and blocking behaviour of WO<sub>3</sub> LB films improved significantly when the thickness was reduced to  $\leq 14$  nm, which is comparable to  $L_D$ . As a result, DSCs fabricated with thinner WO<sub>3</sub> BL (thickness  $\leq 14$  nm) showed significant efficiency ( $\eta$ ) improvement (22%) leading to  $\eta$  up to 9.79% vis à vis DSCs with WO<sub>3</sub> BL having thickness 20 nm.

Received 22nd January 2024,  
Accepted 21st August 2024

DOI: 10.1039/d4ma00063c

rsc.li/materials-advances

## 1. Introduction

In the last decade, dye sensitized solar cells (DSCs) have emerged as potential alternatives to Si solar cell technology on account of their various advantages, such as flexibility, low cost, simple fabrication techniques, lightweight and efficient working even under diffused light.<sup>1,2</sup> The key challenges in developing highly efficient DSCs have been to simultaneously improve the light-harvesting of the active layer and to reduce the recombination losses at various interfaces. Conventionally, a thin transition metal oxide (TMO) film, such as TiO<sub>2</sub> (>50 nm), is employed as an interfacial layer between the FTO substrate and mesoporous TiO<sub>2</sub> (m-TiO<sub>2</sub>) layer (blocking layer, BL) in DSCs, which prevents undesired recombination of photon-generated electrons. This BL also helps in tuning the work function and providing better interfacial properties to enable efficient electron transport.<sup>3–5</sup> In addition to TiO<sub>2</sub>, other metal oxide films such as SnO<sub>2</sub>, Fe<sub>2</sub>O<sub>3</sub>,

ZnO and Nb<sub>2</sub>O<sub>5</sub> have also been employed as BL in DSCs in order to enhance efficiency.<sup>6</sup>

WO<sub>3</sub> has been used extensively for a variety of applications, such as smart windows,<sup>7</sup> photocatalysts and gas sensors, because of its excellent chemical stability, high work function ( $\sim 6.2$  eV) and carrier mobility ( $5\text{--}12$  cm<sup>2</sup> V s<sup>-1</sup>), and tunability of electronic structures through the polymorph.<sup>8–11</sup> However, WO<sub>3</sub> films in solar cells have not been used much as interfacial layers due to low conductivity, amorphous structure, mediocre interfacial charge transfer and unfavorable conduction band (CB) position.<sup>12,13</sup> Therefore, it is essential to achieve high crystallinity, uniformity, and transparency with suitable work function in WO<sub>3</sub> films so that it can provide preferential percolation paths for the charge transport without compromising optical transmittance.<sup>14,15</sup> Furthermore, it has been reported in the literature that reducing the thickness of a uniform TMO film to the Debye length (characteristic length of the space charge layer in the TMO,  $L_D$ ) will yield higher electrical conductivity without compromising optical transmittance.<sup>16</sup> The  $L_D$  is dependent on the dielectric constant ( $\epsilon$ ) and carrier density ( $N_D$ ) as follows:

$$L_D = \sqrt{\frac{\epsilon k T}{q^2 N_D}} \quad (1)$$

<sup>a</sup> Technical Physics Division, Bhabha Atomic Research Centre, Trombay, Mumbai 40085, India. E-mail: vibhas@barc.gov.in

<sup>b</sup> Chemistry Division, Bhabha Atomic Research Centre, Trombay, Mumbai 40085, India

<sup>c</sup> Department of Physics, Guru Nanak Dev University, Amritsar 143005, India

<sup>d</sup> Homi Bhabha National Institute, Mumbai 40094, India

† Electronic supplementary information (ESI) available. See DOI: <https://doi.org/10.1039/d4ma00063c>



where  $k$ ,  $T$  and  $q$  are the Boltzmann constant, temperature and unit charge, respectively.

The  $L_D$  of the  $\text{WO}_3$  is reported to be in the range of 2–20 nm and therefore, it is anticipated that  $\text{WO}_3$  films having thickness in this range ( $<20$  nm) could lead to charge transport behavior different from what is observed for thicker films ( $>20$  nm).<sup>17</sup> Moreover, for TMO having thicknesses  $\leq L_D$ , the space charge layer (SCL) can extend beyond the film thickness. This will eventually lead to different charge distributions near the film–substrate interface and hence, influence the interfacial properties such as charge transport and blocking behavior. Even though reducing the BL thickness is known to be effective for improving the interfacial properties without loss of optical transmittance, preparing such an ultra-thin ( $<20$  nm) uniform film is challenging.

Amongst available techniques to deposit ultra-thin films, sputtering, pulsed layer deposition (PLD), atomic layer deposition (ALD) and molecular beam epitaxy (MBE) have been used widely<sup>18–22</sup> for depositing  $\text{WO}_3$  films. The films, prepared by thermal evaporation, resulted in amorphous structure and rough morphology. Post annealing ( $>300$  °C) employed to induce crystallization, however, led to shrinkage of the material, forming wide cracks owing to the increase in overall residual stresses in the film.<sup>23</sup> Spark ablation was also used to prepare ultra-thin  $\text{WO}_3$  films, and enhanced  $\text{NO}_2$  gas sensing was reported.<sup>24</sup> However, the films had many cracks in as-deposited as well as annealed films. Mattoni *et al.* reported crystalline ultra-thin  $\text{WO}_3$  (9 nm) on top of  $\text{TiO}_2$ -terminated  $\text{SrTiO}_3(001)$  substrates using the PLD technique.<sup>25</sup> The film decorated with Pt resulted in increased sub-ppm hydrogen sensing owing to the crystalline structure and high surface area–volume ratio.<sup>26</sup> Ultra-thin  $\text{WO}_3$  films were also produced using ALD from different precursors such as  $\text{WF}_6$ , *in situ*-generated hexavalent tungsten oxyfluoride,  $(t\text{BuN})_2(\text{NMe}_2)_2\text{W}$ , and hexacarbonyl precursor  $\text{W}(\text{CO})_6$ .<sup>27</sup> However, low growth per cycle ( $<0.2$  Å), high impurity incorporation, and non-stoichiometric composition limited their use for device applications. Furthermore, a plasma-enhanced ALD process was reported, however, a polycrystalline film of monoclinic phase could be obtained only at elevated temperature  $\sim 400$  °C.<sup>28</sup> Though ALD has the advantages of atomic level conformal coverage of a high quality and crystalline film on the substrate, high material cost and consumption as well as high wastage limits the industrial applicability of this technique. Therefore, present techniques for depositing ultra-thin  $\text{WO}_3$  films have the following disadvantages: (i) limited control over the quality of deposited films of different thicknesses, (ii) the necessity of specific substrates, corrosive precursor or co-reactants, (iii) the requirement of high vacuum and high deposition temperature and (iv) non-scalability. Therefore, the reported literature on BL materials in solar cells has mainly been focused on materials which could provide full coverage of the FTO substrate without loss of optical transmittance. It is to be emphasized here that the effect of BL thickness on the DSC performance has not been studied extensively for film thicknesses  $<20$  nm due to the limitation of uniform film coverage by most of the reported

preparation techniques<sup>6,18,19</sup> and therefore, there is a lot of room for developing alternative materials for enhancing device efficiency through maximizing intrinsic BL properties.

In this context, the Langmuir–Blodgett (LB) technique is a very simple, environment-friendly, and versatile method for preparing ordered multilayers of a wide range of materials, such as carbon nanomaterials, conductive polymers, *etc.* with low consumption of materials. In addition, this technique allows control over the morphology, thickness and molecular architecture of films through suitable manipulation of the subphase pH, barrier speed, deposition speed, and post-transfer treatments along with the possibility of low temperature processing. In the present work, crystalline ultra-thin (4–20 nm)  $\text{WO}_3$  films were prepared from the thermal decomposition of the  $\text{WO}_3$ -octadecyl amine (ODA) complex ( $\text{WO}_3\text{ODA}$ ) of multilayers, using the LB technique. The interfacial properties of the prepared films were thoroughly characterized using UV-Vis spectroscopy, electrochemical techniques, ellipsometry, Kelvin-probe and field-emission scanning electron microscopy (FESEM). A significant improvement in blocking and charge transport behavior is observed for films thinner than  $\leq 14$  nm (within  $L_D$  regime) as compared with thick 20 nm  $\text{WO}_3$  films (beyond the  $L_D$  regime). The films, when employed in the fabrication of DSCs, show significant improvement in efficiency ( $\eta$ ) up to 9.79% as compared to those with thicker ( $>L_D$ )  $\text{WO}_3$  BL films ( $\eta \sim 8.02\%$ ). The electrochemical impedance spectroscopy (EIS) and intensity-modulated photocurrent/photovoltage spectroscopy (IMVS/IMPS) data suggested improved charge transport and reduced recombination in DSCs with thinner ( $\leq L_D$ )  $\text{WO}_3$  BL as compared with those with thick BL ( $>L_D$ ).

## 2. Experimental section

Chloroform and other chemicals were of analytical grade or higher purity and were used without any further purification. Deionized (DI) water (Milli-Q, Millipore) having resistance 18 M $\Omega$  was used to prepare solutions. The preparation of LB multilayers of  $\text{WO}_3\text{ODA}$  was carried out using a KSV-Nima Langmuir trough equipped with two Teflon barriers with a total area of 850 cm<sup>2</sup>. The absence of surface-active contaminants was verified by compressing the subphase to achieve surface pressure  $\leq 0.1$  mN m<sup>-1</sup>. Then, 50  $\mu\text{L}$  of octadecyl amine solution in chloroform (1 mg mL<sup>-1</sup>) was spread on the subphase containing 0.15 mM sodium tungstate solution (pH  $\sim 7$ ) in DI water, using a Hamilton micro-syringe. After 20 mins to evaporate solvent, the layer was simultaneously compressed by two compression barriers at the rate of 5 mN m<sup>-1</sup> min<sup>-1</sup>. The FTO substrates were cleaned by successive sonication in warm Hellmox soap, DI water, acetone, methanol, and isopropyl alcohol and then dried with nitrogen gas, whereas Si substrates were cleaned using a Piranha solution. All substrates were further cleaned by using atmospheric plasma (Harrick Plasma, model PDC-002) in ambient air for 10 min before carrying out multilayer deposition. Multilayers were transferred in successive downstrokes and upstrokes with a 10 min interval between the upstroke and the subsequent downstroke. The dipping rate



was 5 mm min<sup>-1</sup> in both directions. The transfer of the LB multilayers was Y type and the transfer ratio was 90–100% onto FTO and Si substrates. The films were subsequently thermally decomposed at 400 °C for 5 h. In order to compare the results, WO<sub>3</sub> films were also prepared by spin casting, using a neutral surfactant-(polyethylene glycol) assisted tungsten precursor as reported earlier.<sup>29</sup> The thickness of the prepared films on Si substrates was estimated using variable angle spectroscopic ellipsometry (Sentech SE400adv) at wavelength 632 nm. For device fabrication, a slightly modified procedure of preparing photoanode in our earlier work was adopted.<sup>30</sup> The photoanode was prepared by doctor blading mesoporous TiO<sub>2</sub> paste (Solaronix, Ti-nanoxide T/SP) and a scattering layer of TiO<sub>2</sub> paste (Solaronix, Ti-nanoxide R/SP) on the plasma treated WO<sub>3</sub> BL/FTO substrate. The films were sintered at 500 °C using a multi-step temperature program. This was followed by a post-treatment with 40 mM TiCl<sub>4</sub> aqueous solution at 70 °C for ½ h and subsequently annealing at 500 °C for ½ h. The photoanodes were sensitized using a solution of 0.5 mM N719 dye (Solaronix) with 5 mM cholic acid in *tert*-butyl alcohol/acetonitrile (1 : 1 v/v). The devices (area 0.12 cm<sup>2</sup>) were fabricated using a pre-drilled platinum coated counter electrode. The electrochemical as well as photovoltaic characterization was performed using a Potentiostat/Galvanostat (PGSTAT 30, Autolab Eco Chemie, Netherlands). The surface morphology was analyzed using a FESEM (Carl Zeiss Supra 55, SEM micrograph) as well as atomic force microscopy (AFM) (Anton Paar Tosca TM 400) in tapping mode. UV-Vis spectroscopy was carried out using a double beam UV-Vis spectrophotometer (Jasco, V 530). The Fourier transform infrared spectroscopy (FTIR) of LB films deposited on Si substrates was carried out, in reflectance mode, using a Bruker spectrometer (model: Vertex 80 V) at a resolution of 4 cm<sup>-1</sup>. X-ray photoelectron spectroscopy (XPS) data measurements were carried out using the RIBER MBE system, which was equipped with a Mg K<sub>α</sub> source. The binding energy scale was calibrated to the Au 4f<sub>7/2</sub> line of 83.95 eV. Raman spectra of LB films, deposited on Si substrates, were recorded on a Jobin-Yvon micro-Raman spectrometer (LabRAM HR800), in the 180° backscattering geometry, with a spectral resolution of 1 cm<sup>-1</sup> using a HeNe Laser.

The laser beam was focused onto the sample using a ×100 objective lens and the laser spot size was ~5 μm. Kelvin probe scanning microscopy (model: KP Technology), having resolution of ~0.003 eV, was employed to measure the work function of spin cast and LB WO<sub>3</sub> films on FTO substrates. Electrochemical characterizations of all BLs were carried out using a one-compartment, three-electrode electrochemical cell: FTO or FTO/WO<sub>3</sub> performed as the working electrode, while Ag/AgCl and platinum electrodes were used as reference and counter electrodes, respectively. The EIS measurements were done in a range from 100 mHz to 500 kHz by applying an AC voltage of 10 mV superimposed on a dc voltage. For dark EIS measurements, data were collected at dc bias of open-circuit voltage ( $V_{OC}$ ),  $V_{OC} \pm 0.02$  V and  $V_{OC} \pm 0.04$  V. The results were analyzed using an equivalent circuit model fitted with ZSimpWin 3.22 software. IMPS/IMVS measurements were carried out under a Green LED (wavelength 530 nm), which provided the DC illumination bias, superimposed with AC modulation ~10% of the DC intensity. The measurements were performed between 1 kHz and 100 mHz, 20 data points per decade. The current–voltage ( $J$ – $V$ ) characteristics of the DSCs were recorded under 1 sun simulated AM 1.5G illumination using a solar simulator (G2V, Canada). The intensity of the source was calibrated using a reference silicon cell before recording the characteristics.

### 3. Results and discussion

#### 3.1 Surface properties of the WO<sub>3,ODA</sub> monolayer and structure of WO<sub>3,ODA</sub> Langmuir–Blodgett multilayers

Since the lateral organization of the ODA molecules on the subphase may influence the WO<sub>3,ODA</sub> monolayer formation and subsequent multilayer deposition, the surface properties of monolayer organization and packing were investigated by recording surface pressure–mean molecular area ( $\pi$ – $A$ ) isotherms and are presented in Fig. 1(a). At large area, *i.e.* at the start of barrier compression, (zero surface pressure) a gas phase at the air–water interface is observed. The presence of WO<sub>4</sub><sup>2-</sup> ions in the subphase results in an increased expansion of the

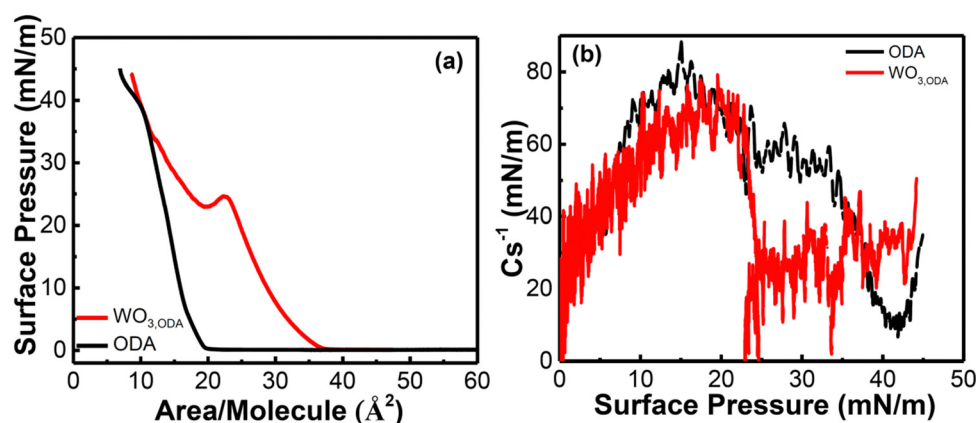


Fig. 1 (a) Surface pressure isotherm and (b) compressibility of ODA and WO<sub>3,ODA</sub> monolayers.



ODA monolayer as evident by an increase in the lift-off area ( $36.8 \text{ \AA}^2$ ) of the ODA monolayer spread on tungstate salt subphase. Distinct transition phases can be observed in the presence of  $\text{WO}_4^{2-}$  ions in the subphase, which indicates an interaction between  $\text{WO}_4^{2-}$  ions and ODA. This interaction occurs because the ODA molecules undergo protonation in the presence of water resulting in positive head groups ( $\text{R-NH}_3^+$ ). This positive charge interacts with anionic  $\text{WO}_4^{2-}$ , resulting in an electrostatic interaction between the two groups. In the range  $10\text{--}20 \text{ mN m}^{-1}$ , it is more clearly discerned in the presence of  $\text{WO}_4^{2-}$  ions than in pure water isotherms where transition phases occur suddenly because of fast condensation of the ODA molecules. Moreover, an additional slope change takes place around  $25 \text{ mN m}^{-1}$ , where a kink is observed. When ODA is compressed beyond this, a steep slope of the  $\pi$ - $A$  curve is observed, indicating a phase transition. This is different for the isotherm of the ODA monolayer, for which the lift off area  $\sim 21 \text{ \AA}^2$  per molecule is estimated, consistent with the reported values found in the literature.<sup>31</sup> Transition phases are not observed in this isotherm, suggesting that a direct transition from a gas to a condensed phase takes place. In order to further elucidate phase transitions and to characterize the interactions of  $\text{WO}_4^{2-}$  ions with the ODA monolayer, as well as to examine changes in the interfacial packing properties, two-dimensional compressibility of the Langmuir monolayers was investigated. The compressibility coefficient was calculated as per the following equation:

$$C_s^{-1} = A \frac{d\pi}{dA} \quad (2)$$

while  $C_s^{-1}$  is low in the gas phase, it increases at the liquid-expanded (LE) and liquid-condensed (LC) phases due to difficulty in deforming the monolayer. The maximum values of the  $C_s^{-1}$  provide information on the monolayer phase: the values in the range of  $100\text{--}250 \text{ mN}$  have been associated with the LC phase, and solid phase.<sup>32</sup> Fig. 1(b) shows the isothermal compressibility of the  $\text{WO}_3$ , ODA as well as ODA monolayer at the air-water interface. As shown in the figure, for both cases, the  $C_s^{-1}$  value increases as the molecules reorganize to a more condensed state. After the maximum, the condensed state is completed and the  $C_s^{-1}$  decreases. For ODA on pure water, a steady increase of the surface pressure starting from 0 to  $15 \text{ mN m}^{-1}$  was observed,

and after  $15 \text{ mN m}^{-1}$ , the modulus decreases. The  $C_s^{-1}$ - $\pi$  curve for ODA monolayers on subphase containing  $\text{WO}_3$  salt is entirely different from that of ODA monolayers on pure water. Two peaks can be distinguished in the figure at  $15\text{--}20 \text{ mN m}^{-1}$  and  $38\text{--}40 \text{ mN m}^{-1}$ , clearly suggesting a phase transition. Lower values of  $C_s^{-1}$  were obtained for  $\text{WO}_3$ , ODA as compared to that of ODA monolayers suggest low rigidity and compaction of the  $\text{WO}_3$ , ODA monolayer. The difference in  $C_s^{-1}$ - $\pi$  curves in the LC region confirms molecular interactions of  $\text{WO}_4^{2-}$  anions with ODA molecules. Since the  $\text{WO}_3$ , ODA monolayer is the building block of the  $\text{WO}_3$  films and close packed at the maximum point in the  $C_s^{-1}$ - $\pi$  curve, we chose surface pressure corresponding to this lowest  $C_s$  ( $\sim 15 \text{ mN m}^{-1}$ ) to deposit multilayers. For this purpose,  $\text{WO}_3$ , ODA monolayers were transferred to the substrate at constant pressure multiple times and were subsequently decomposed thermally. The phase/structure of the multilayered films after thermal decomposition was investigated using FTIR, XPS, and Raman spectroscopy (Fig. 2). As shown in Fig. 2(a), the FTIR spectra of the thermally decomposed film showed significant reduction of the C-H stretching vibration bands of the hydrocarbon chains at  $2919 \text{ cm}^{-1}$  (asymmetric) and  $2851 \text{ cm}^{-1}$  (symmetric) and complete removal of the C-H bending mode, at  $1470 \text{ cm}^{-1}$ , of the  $\text{CH}_2$  group. It is to be noted that these peaks were clearly observed in the  $\text{WO}_3$ , ODA films. This confirms that the hydrocarbon part in  $\text{WO}_3$ , ODA is removed after thermal decomposition. The stoichiometric  $\text{WO}_3$  phase was confirmed by X-ray photoelectron spectroscopy (Fig. 2(b), which when deconvoluted, show peaks corresponding W  $4f_{5/2}$  and  $4f_{7/2}$  doublet peaks at  $37.9 \text{ eV}$  and  $35.8 \text{ eV}$ , respectively ( $\text{W}^{6+}$  state) and in accordance with the reported literature values for  $\text{WO}_3$ .<sup>33</sup> It should be noted that the de-convoluted core level spectrum for the spin cast  $\text{WO}_3$  film showed (i) a shifting of  $0.7 \text{ eV}$  towards higher binding energy for doublet peaks, *i.e.* the appearance of W  $4f_{5/2}$  and W  $4f_{7/2}$  peaks at  $38.6 \text{ eV}$  and  $36.5 \text{ eV}$ , respectively and (ii) two smaller contributions from the second doublet at lower binding energy, (W  $4f_{5/2} = 37.9 \text{ eV}$  and W  $4f_{7/2} = 35.8 \text{ eV}$ , in addition to peaks for W  $4f_{7/2}$  and W  $4f_{5/2}$  states. This suggests sub-stoichiometry and the existence of defects due to the presence of  $\text{W}^{5+}$  states in the spin cast film.<sup>33</sup> A shift in doublet, observed in spin cast films, towards higher binding energy as relative to stoichiometric  $\text{WO}_3$  has been attributable to the presence of a large degree of oxygen deficiency and thereby

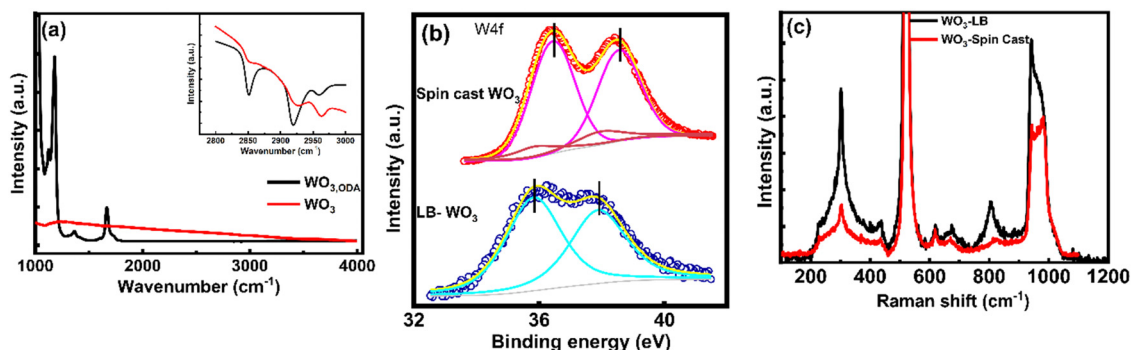


Fig. 2 (a) FTIR of the  $\text{WO}_3$  LB film after thermal decomposition, (b) XPS and (c) Raman spectra of the spin cast and  $\text{WO}_3$  LB film.



lattice disorder in hydrogen-treated  $\text{WO}_3$  films. Large amounts of lattice disorder result in occupation of large density of states within the energy gap with a corresponding shift of the Fermi level toward higher energies. Other than stoichiometry, spin cast and LB  $\text{WO}_3$  films also differ in their crystallinity as depicted in Raman data (Fig. 2(c)). The features at 303, 435, 622, and 675  $\text{cm}^{-1}$  show the presence of Si-O bonds due to the substrate.<sup>34</sup> A well-defined peak at  $\sim 810 \text{ cm}^{-1}$  is observed for  $\text{WO}_3$  LB films confirming the formation of the tetragonal phase of  $\text{WO}_3$  as observed earlier for ultra-thin films. Two major features are observed in the case of the spin cast  $\text{WO}_3$  film: the peak at 810  $\text{cm}^{-1}$  is (i) red-shifted to 826  $\text{cm}^{-1}$  owing to the bulk-nature of the spin cast films and (ii) significantly weakened in intensity due to reduced crystallinity.<sup>35</sup> This is consistent with XPS data, which shows increased defect states corresponding to the sub-stoichiometric phase in the spin cast  $\text{WO}_3$  films.

### 3.2 Optical, morphology and blocking properties of ultra-thin $\text{WO}_3$ films

After establishing the fact that thermal decomposition of the  $\text{WO}_{3,\text{ODA}}$  multilayered films yields a stoichiometric and crystalline  $\text{WO}_3$  structure, we prepared  $\text{WO}_3$  films of various thicknesses by controlling the deposition cycle of  $\text{WO}_{3,\text{ODA}}$  monolayers on the substrate. Different numbers of monolayers, 9, 19, 25, 35 and 50 layers, were deposited and hereafter will be referred to as 9 L, 19 L, 25 L, 35 L and 50 L, respectively. The optical, morphology and interfacial properties of the prepared  $\text{WO}_3$  film were studied before employing them as BLs in DSC fabrication and the results are presented as follows:

Since the optical transmittance is strongly affected by dielectric constants, we estimated thickness and optical constants (refractive index,  $n$  and extinction coefficient,  $k$ ) using ellipsometric measurements and fitted data using the model as reported earlier.<sup>30</sup> The estimated  $n$  and  $k$  of the as-deposited films were found to be in 1.56 and 0.04, respectively. After thermal decomposition, the refractive index ( $\sim 2.8$ ) increases and the absorption coefficient decreases ( $\sim 0.006$ ), suggesting conversion of the  $\text{WO}_{3,\text{ODA}}$  LB multilayers to  $\text{WO}_3$ . The high refractive index of all  $\text{WO}_3$  films suggests compact and uniform deposition of the film. The thicknesses of the  $\text{WO}_3$  multilayers,

transferred on Si substrates, were estimated using estimated  $n$  and  $k$  values and are presented in Fig. 3(a) as a function of number of layers. The thickness of the as- $\text{WO}_3$  film was found to shrink approximately 1/6th after thermal decomposition. The estimated data reveal that a monolayer of  $\text{WO}_{3,\text{ODA}}$  is  $\sim 2.4 \text{ nm}$  thick and after thermal decomposition, it reduces to  $\sim 0.4 \text{ nm}$ . It should be noted that as-deposited films were featureless and transparent up to 19 L, and afterwards a semi-transparent film having a brownish tinge was observed. After thermal decomposition, all  $\text{WO}_3$  LB films of thickness  $\leq 14 \text{ nm}$  show enhanced optical transmittance as presented in Fig. 3(b). This might be due to better matching of the refractive index at the FTO/ $\text{WO}_3$ /air interface than the FTO/air interface (refractive index for FTO  $\sim 2.4$ ), which reduces internal reflection and therefore results in enhanced transmittance. Slightly reduced transmittance observed for the 20 nm thick film might be due to increased thickness. Typical fringes observed in the spectra of all  $\text{WO}_3$  LB films suggest smooth surface morphology of the prepared films; in contrast, such fringes were absent in the spin cast  $\text{WO}_3$  film.

The smooth morphologies of the prepared LB films as compared with that of the spin cast film were also confirmed from recorded FESEM images, as depicted in Fig. 4. The FESEM images of  $\text{WO}_3$  films are slightly blurred as compared with FTO (inset of Fig. 4(a)) owing to the ultra-thin nature. As compared to the FESEM image of the spin cast  $\text{WO}_3$  film, LB deposited  $\text{WO}_3$  films were found to be more uniform, pin-hole free and homogeneous. It should be noted that the thickness variation of the  $\text{WO}_3$  film from 4 nm to 20 nm did not result in different surface morphologies. The uniformity in the LB deposited film is also supported by the AFM image, which shows a compact film comprising small crystallites after thermal decomposition of  $\text{WO}_{3,\text{ODA}}$  multilayers (Fig. S1, ESI<sup>†</sup>). It should be noted that though uniform morphologies for  $\text{WO}_3$  crystalline films are observed in the SEM and AFM images, lateral uniformity in  $\text{cm}^2$  area has been assessed in the best manner using cyclic voltammetry.<sup>30,36</sup> Therefore, the thickness dependence of the interfacial properties, such as blocking and charge transport behaviour, were studied by analyzing their cyclic voltammogram (CV), EIS and Mott-Schottky (MS) plots as described in

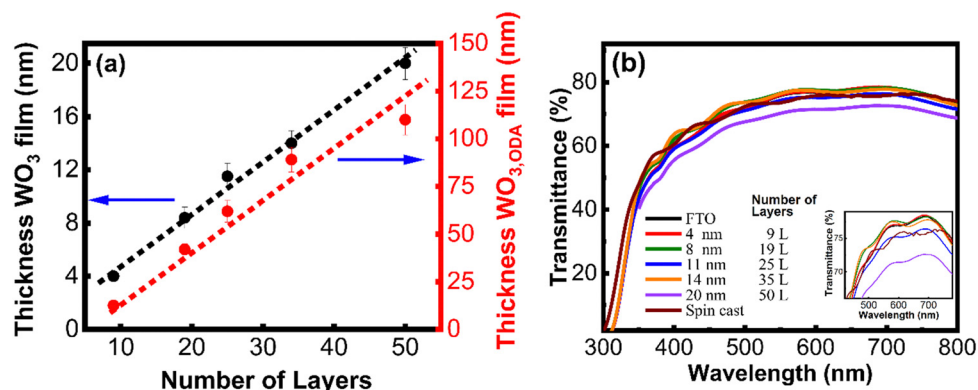


Fig. 3 (a) Estimated thickness and (b) transmittance as a function of number of layers.



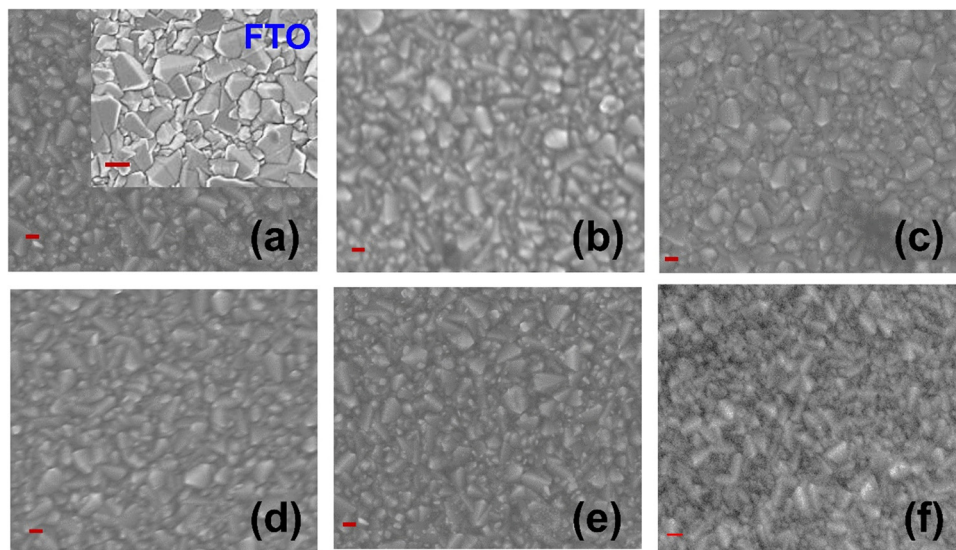


Fig. 4 Top-view FE-SEM images of the prepared  $\text{WO}_3$  LB films of thicknesses (a) 4 nm, (b) 8 nm, (c) 11 nm, (d) 14 nm, (e) 20 nm, and (f) the spin cast film, scale bar  $\sim 200$  nm.

earlier reports<sup>30</sup> (Fig. S2, ESI<sup>†</sup>). The effectiveness of the blocking effect (BE) of the  $\text{WO}_3$  film was estimated by taking into account the percentage suppression of the anodic current in CV as compared to that for the FTO substrate. As shown in Fig. S2(a) (ESI<sup>†</sup>), all  $\text{WO}_3$  LB films showed (i) anodic/cathodic peaks, and (ii) significant suppression of the anodic current as compared to bare FTO and (iii) enhanced cathodic peak, which is due to the electron accumulation below the flat band potential and corresponding reduction of  $\text{Fe}(\text{CN})_6^{3-}$  at the FTO/ $\text{WO}_3$  surface. It is to be noted that  $\text{WO}_{3,\text{ODA}}$  multilayers do not show such features owing to the presence of insulating ODA in the complex. When the film thickness is increased from 4 to 11 nm, good blocking behavior  $>80\%$  is observed, despite the fact that the thickness of the film is very low (Fig. 5(a)). For 14 nm thick film, the blocking effect is slightly increased and then slightly decreases for 20 nm thick films. The peak-to-peak separation ( $\Delta E$ ) of the anodic and cathodic peaks in the CV follows the trend of blocking effect. This is expected as enhanced thickness of the  $\text{WO}_3$  layer poses more and more resistance to charge transfer reaction and therefore the oxidation peak shifts towards positive potential and therefore, results in increased  $\Delta E$ .

In order to investigate further the thickness effect on blocking behaviour, the EIS spectra of various films were recorded (Fig. S2(b), ESI<sup>†</sup>). The measured data were fitted using Randle's equivalent circuit model ( $R([R_{\text{CT}}W]Q)$ ), where  $R$  is the overall contribution of the intrinsic resistance of the  $\text{WO}_3$  film, ionic resistance of the electrolyte, and contact resistance comprising connections to the  $\text{WO}_3$  electrode, and  $R_{\text{CT}}$ ,  $Q$  and  $W$  are the charge transfer resistance, constant phase element and Warburg impedance corresponding to  $\text{WO}_3$  film, respectively. The capacitance ( $C_{\text{film}}$ ) of the  $\text{WO}_3$  film was estimated using estimated  $Q$  and  $R_{\text{CT}}$  values as described earlier<sup>36</sup> and is presented in Fig. 5(b). As shown in the figure, the  $R_{\text{CT}}$  value increased while the  $C_{\text{film}}$  decreased with increasing the thickness from 4 nm to 14 nm. These results are indicative of the formation of dense and compact layers. When the film thickness is increased to 20 nm, a slight decrease in charge transfer resistance is observed. The results are consistent with the cyclic voltammetric results where a similar drop in the blocking effect and  $\Delta E$  has been observed. In order to probe further the thickness dependent interfacial properties of FTO/ $\text{WO}_3$ , we estimated the capacitance ( $C_{\text{sc}}$ ) of the space charge region, which plays a significant role in the charge distribution at the semiconductor–electrolyte

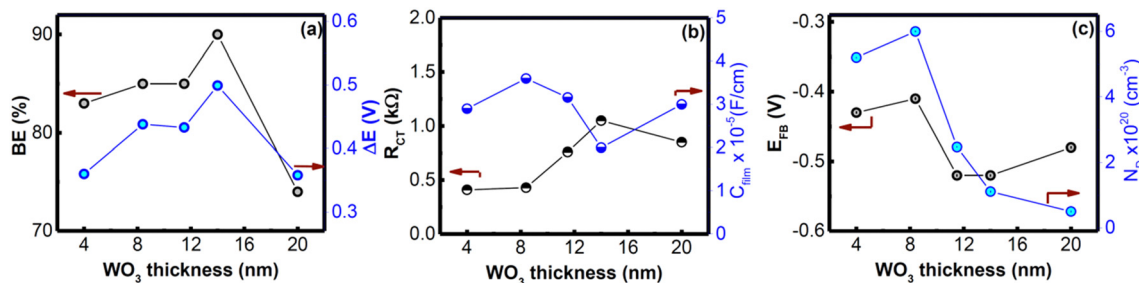


Fig. 5 Estimated (a) blocking effect and  $\Delta E$  from CV curves, (b)  $R_{\text{CT}}$  and capacitance across the  $\text{WO}_3$  film from EIS spectra and (c) carrier density and flat band potential from the MS plots as a function of  $\text{WO}_3$  thickness.



interface. The potential drop in the space charge region, and therefore, the extent of band bending, referred to as  $\phi_{\text{SC}}$  (as depicted schematically in ESI† Fig. S3) is given by the following equation:<sup>37</sup>

$$\phi_{\text{SC}} = \frac{kT}{2e} \left( \frac{W}{L_D} \right)^2 \quad (3)$$

where  $W$  is the depletion width associated with  $\phi_{\text{SC}}$ . The above equation is valid for bulk semiconductors or semiconductors having particle size  $\gg L_D$ . For nanostructured materials having particle size  $\sim L_D$ , minimal to no potential drop is present in the space charge region, and band bending can only be obtained for either very highly doped or relatively lower dielectric constant in the material. Neglecting the Helmholtz capacitance, the relationship between the  $C_{\text{SC}}$  and applied potential is given by the well-known Mott–Schottky equation and has been used to estimate flat band potential ( $E_{\text{FB}}$ ) as well as charge carrier density ( $N_D$ ) in TMO films.<sup>38,39</sup> For BL thicknesses  $\leq 9$  nm, the slope of MS curves is similar to that of FTO for  $\text{WO}_3$  implying that the space charge region fully extends to the FTO region<sup>40</sup> (Fig. S2c, ESI†). It has been suggested that if the space charge region extends into the FTO substrate, the slope of the MS plot is determined only by dielectric constant and the charge carrier density of the FTO substrate and is not influenced by the film deposited on the substrate.<sup>38</sup> Therefore, estimated  $N_D$  and  $E_{\text{FB}}$  parameters for  $\text{WO}_3$  films having thickness  $< 11$  nm, are not representative of the  $\text{WO}_3$  film. Nevertheless, when the film thickness is increased to 11 nm and beyond, a drastic change in slope occurs; therefore, MS plots may be used to determine  $E_{\text{FB}}$  and  $N_D$  values. As shown in Fig. 5(c), the  $E_{\text{FB}}$  shifts negatively with increasing layer thickness  $\geq 11$  nm and stabilizes thereafter, suggesting that the dielectric properties of the  $\text{WO}_3$  are now dominating the interface properties. Similar kinds of thickness dependent shift in  $E_{\text{FB}}$  have been observed in the ALD  $\text{TiO}_2$  layers and have been attributed to the fact that the (i) crystalline structure starts to be detectable for films thicker than  $\sim 15$  nm and (ii) for thinner films  $E_{\text{FB}}$  is largely determined by the FTO substrate.<sup>41</sup> As reported earlier for  $\text{WO}_3$  film, the position of CB can be approximated to near  $E_{\text{FB}}$ <sup>42</sup> and therefore, the change in  $E_{\text{FB}}$  is correlated with CB position. This means that the conduction

band (CB) position of  $\text{WO}_3$  is altered depending on the BL thickness in regimes, defined as thick film (20 nm) and thin films ( $\leq 11$  nm). Subsequently, the interfacial properties, such as the charge transport and recombination, will also differ in both regimes. Furthermore, the decreased charge carrier density for films thicker than 11 nm may be related to the onset of bulk properties of the films as also observed for  $\text{TiO}_2$ ,  $\text{NiO}$  and  $\text{SnO}_2$  films<sup>16,43</sup> and is consistent with CV results, which shows reduced accumulation current for films thicker than 11 nm (Fig. S2, ESI†). A drastic change in the carrier density observed for  $\text{NiO}$  and  $\text{SnO}_2$  films with thickness reduction has been attributed to the space-charge effect as governed by  $\phi_{\text{SC}}$ . For carrier density in  $\text{WO}_3$  films ranging from  $0.5\text{--}5 \times 10^{20} \text{ cm}^{-3}$ , the calculated  $L_D$  is 2–4 nm. Therefore, for film thickness up to 14 nm ( $\sim 2\text{--}3L_D$ ), the  $\phi_{\text{SC}}$  is very small and so negligible band bending occurs at the FTO/ $\text{WO}_3$  interface. This leads to an efficient electron transfer across the FTO/ $\text{WO}_3$  interface. For films having thickness  $\sim 20$  nm, which is large compared to the  $L_D$ , the films are bulk-like. This gives rise to large  $\phi_{\text{SC}}$  and thereby, large band bending at the FTO/ $\text{WO}_3$  interface. The presence of a barrier, therefore leads to reduced electron transfer at the FTO/ $\text{WO}_3$  interface. This, in turn, enhances the recombination probability at the interface and leads to reduced charge collection at the FTO/ $\text{WO}_3$  interface. As a result of sluggish charge transport, thicker films (20 nm) show slightly reduced blocking efficiency than thinner films ( $\leq 14$  nm).

### 3.3 Influence of $\text{WO}_3$ BL thickness on photovoltaic properties

The effect of the variation of the thickness of the blocking  $\text{WO}_3$  layer on DSCs performance was studied by recording current density ( $J$ )–voltage ( $V$ ) curves under AM 1.5 illumination and in the dark (Fig. 6a and b). All devices showed high efficiency (8% or greater) as compared with the DSC fabricated with spin cast  $\text{WO}_3$  BL, which shows low efficiency ( $\sim 7\%$ ) due to low fill factor (FF) and  $V_{\text{OC}}$ . The DSCs prepared using spin cast films show good short-circuit current density ( $J_{\text{SC}}$ ), which is comparable with that of  $\text{WO}_3$  LB. This might be due to the fact that the work function ( $\Phi$ ) values for spin cast and LB films are close to the ionization potential of FTO ( $\Phi_{\text{FTO}} \sim 5.1$  eV) (Fig. S4, ESI†). Owing to the small difference, ohmic-like contact (Fig. S3a, ESI†)

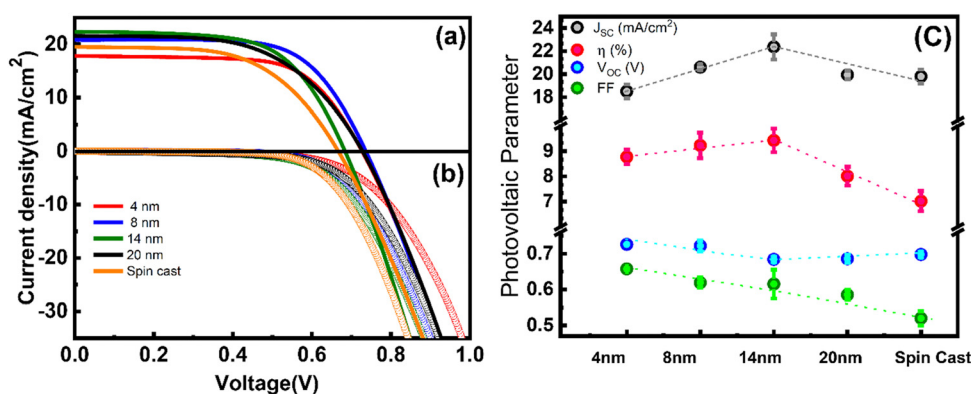


Fig. 6 (a) Typical photovoltaic (solid circles) and (b), dark characteristics (open circles) and (c) average values of estimated photovoltaic parameters of three DSCs, fabricated using BL of different thickness along with error values, under 1.5AM illumination (dashed lines are a guide for the eyes).



forms in both cases, resulting in comparable  $J_{SC}$ . Furthermore, there is a clear distinction in efficiency for DSCs fabricated with  $WO_3$  BL thickness  $\leq 14$  nm and those with thickness  $\sim 20$  nm. The  $J_{SC}$ , FF and  $V_{OC}$  decrease with increase in the  $WO_3$  blocking layer thickness to 20 nm, which is well above the  $L_D$  and is attributable to the bulk-effect.

Similar observations were reported for perovskite solar cells fabricated with ultra-thin films of NiO and  $SnO_2$  as interfacial layers.<sup>16,43</sup> Seo *et al.* found that when the NiO film thicknesses decreased from 10–15 to 2.5–7.5 nm, the short-circuit current ( $J_{SC} \sim 16.5$  to  $\sim 18.5$  mA cm<sup>-2</sup>) increased due to the improved conductivity of the film as the thickness is sufficient to be overlapped by  $L_D$ . In the case of the  $SnO_2$  film, when the thickness is increased just above the  $L_D$  value, improvement in all photovoltaic parameters was observed due to enhanced charge extraction.<sup>43</sup> In both cases, the device efficiency decreased when the thicknesses of the buffer layer increased much higher than the Debye length. Since the thickness of the prepared  $WO_3$  BL (4–14 nm) is less than the reported Debye length of  $WO_3$ , the improvement in the  $J_{SC}$  of the devices is due to nano effects. Beyond this thickness, the bulk property dominates and therefore, the  $J_{SC}$  decreases owing to the decrease in conductivity. Slightly reduced  $J_{SC}$  observed in DSCs fabricated with 4 nm  $WO_3$  BL might be due to the limitation of FTO surface roughness, therefore resulting in slightly reduced efficiency. Nevertheless, improved  $V_{OC}$  and FF obtained for these devices are attributed to the fact that the thickness of BL is of the order of  $L_D$ . In this case, the  $WO_3$  film is fully depleted, having minimal potential drop in the BL, as discussed in the earlier section for MS analysis. Improved charge transport and reduced recombination for DSCs employing thinner BLs ( $\leq L_D$ ) as compared to that having thicker BL ( $> L_D$ ) therefore gives rise to improved  $J_{SC}$  and FF and thereby enhanced efficiency. In all, high efficiency ( $\sim 9.79\%$ ) observed for DSCs employing 14 nm thick  $WO_3$  BL is the result of enhanced carrier density, conductivity, and the uniform and homogeneous surface, as well as excellent blocking behaviour as observed earlier. It is to be emphasized here that even a 4 nm thick  $WO_3$  blocking layer is sufficient to serve the purpose of the blocking layer without compromising  $V_{OC}$  and FF.

To further investigate the influence of BL thickness on the device performance, we focus on dark current (Fig. 6(b)), which is generally dominated by the recombination through

nanocrystalline  $TiO_2$  particles or the exposure of the FTO substrate to the electrolyte. The onset potential for 4 nm thick  $WO_3$  film is observed at voltage  $> 0.56$  V and shifts to lower potential 0.48 V for a  $WO_3$  film thickness of 20 nm, in accordance with the  $JV$  data where a slight decrease in FF is observed for DSCs employing  $WO_3$  BL. This result is consistent with earlier reports where thinner films have provided better charge extraction due to the space charge region effect.<sup>43</sup> In all, DSCs fabricated with BL of thickness  $\leq 14$  nm reveal better  $J_{SC}$ , FF,  $V_{OC}$  and efficiency as well as reduced dark current as compared to DSCs employed with BL of thickness  $\sim 20$  nm.

To substantiate the above findings, we investigated the devices further using impedance spectroscopy, under illumination as well as dark conditions (Fig. S5, ESI<sup>†</sup>). Various parameters, such as chemical capacitance ( $C_\mu$ ), recombination time, series resistance ( $R_s$ ) and charge transfer resistance ( $R_{PT}$ ) were estimated by fitting the Nyquist plots using the electrical circuit as described in Fig. S5(f) (ESI<sup>†</sup>)<sup>3,4</sup> and are presented in Fig. 7. The electrical circuit elements contributing to the photoanode impedance are dependent on the illumination as well as potential conditions as discussed below:

(i) EIS under 1 sun:

Under 1 sun illumination and at a potential equal to the open circuit potential, the chemical capacitance  $C_\mu$ , represents the density of photogenerated electrons arising due to charge accumulation at the photoanode/electrolyte interface. The estimated  $R_s$  for DSCs comprises the bulk resistance of the photoanode, and contact resistance of all interfaces and the counter electrode as well as the connection resistance. Since all DSCs have the same layers except that the thickness of  $WO_3$  BL is varied, any variation in  $R_s$  value may be attributable to the FTO/ $WO_3$  and  $WO_3$ /m- $TiO_2$  interface. As shown in the figure, a slightly higher  $R_s$  is observed for DSCs having BL of thickness  $\leq 9$  nm than that for BL of thickness 14 nm, and this is attributable to the presence of fully depleted regions in thinner  $WO_3$  BL as evident from MS results discussed earlier in Section 3.2. Furthermore, the recombination time and  $C_\mu$  does not change much for DSCs fabricated with BL thickness  $\leq 14$  nm. However, a sudden drop is observed for DSCs based on 20 nm  $WO_3$  BL. The high values of chemical capacitance and recombination suggest better charge transport and reduced recombination, leading to higher  $J_{SC}$ ,  $V_{OC}$

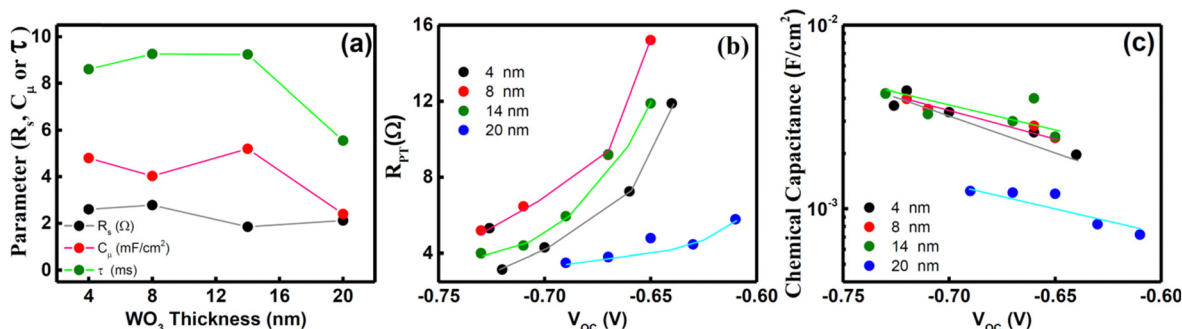


Fig. 7 (a) Extracted EIS parameters,  $R_s$ ,  $C_\mu$  and  $T$  from the EIS spectra recorded at  $V_{OC}$  of the respective device under AM 1.5 sun illumination and, estimated (b) charge transfer resistance and (c) chemical capacitance from dark EIS curves as a function of thickness of the  $WO_3$  BL.



and FF for DSCs employing  $\text{WO}_3$  BL of thickness  $\leq 14$  nm. This is consistent with our earlier observation on the CV and EIS results of  $\text{WO}_3$ , where a high carrier density and charge transfer resistance is associated with thinner  $\text{WO}_3$  films (thickness  $\leq 14$  nm) and corroborates  $JV$  data.

(ii) Dark EIS:

Under dark conditions, the photoanode is insulating as no photoexcited electrons are injected into the conduction band of mesoporous  $\text{TiO}_2$  and the value of recombination resistance is higher than that in 1 sun. This is due to the fact that the  $\text{I}_3^-$  is formed in proximity to the counter electrode and then it has to diffuse through the electrolyte before reaching the photoanode. The chemical capacitance ( $C_{m-\text{TiO}_2}$ ) in this case arises mainly due to localized electron trapping states and therefore, accounts for the electron recombination at the  $m\text{-TiO}_2/\text{electrolyte}$  interface. Furthermore, the  $C_{m-\text{TiO}_2}$  of the  $\text{FTO}/\text{WO}_3/m\text{-TiO}_2$  photoanode in the dark shows an exponential rise with decrease in applied voltage. This is a behavior typical of the photoanode and is related to the total density of electrons in the dark,  $n$ , by the expression:<sup>44</sup>

$$C_{m-\text{TiO}_2} = \frac{ne^2}{kT} \quad (4)$$

where  $n \propto n_{\text{CB}}^\beta$  and  $1 > \beta > 0$  indicate an exponential distribution of traps below the conduction band edge.

The parameters deduced from dark EIS measurements, such as charge transfer resistance ( $R_{\text{PT}}$ ) and  $C_{m-\text{TiO}_2}$  of the

$m\text{-TiO}_2/\text{electrolyte}$  interface corroborate the EIS results under 1 sun. A clear distinction between DSCs employing BL having thickness  $\leq 14$  nm and 20 nm is observed in the  $R_{\text{PT}}-V_{\text{OC}}$  and  $C_{m-\text{TiO}_2}-V_{\text{OC}}$  curves, as shown in Fig. 7(b) and (c). The  $R_{\text{PT}}$  value increases exponentially with increase in the  $V_{\text{OC}}$ , and is consistent with earlier reports.<sup>44</sup> Higher  $R_{\text{PT}}$  values obtained for DSCs having  $\text{WO}_3$  BL of thickness  $\leq 14$  nm, suggests reduced charge recombination at the  $m\text{-TiO}_2/\text{electrolyte}$  interface. A high value of  $C_{m-\text{TiO}_2}$  observed in DSCs having BL of thickness  $\leq 14$  nm indicates reduced charge carrier density and therefore fewer defects as compared with that of DSCs with BL of thickness 20 nm.

The improved interfacial properties of the DSCs fabricated with BL of thickness  $\leq 14$  nm are further confirmed from IMVS and IMPS measurements (Fig. 8). IMPS and IMVS curves do not show much variation in shape when the thickness of the BL in DSC is varied from 4 nm to 14 nm. However, the DSCs fabricated with 20 nm and spin cast  $\text{WO}_3$  film revealed development of an additional arc at lower frequency suggesting changes in the kinetics at the  $\text{FTO}/\text{WO}_3$  interface. The appearance of an arc may be related to recombination due to the bulk-nature of the film.<sup>45</sup> The transport and recombination time for the device were calculated from the expression  $T_n = 1/2\pi f_n$  and  $T_R = 1/2\pi f_R$ , respectively, where  $f_n$  (or  $f_R$ ) is the characteristic frequency minimum of the imaginary component from the IMPS (or IMVS) data. The figure reveals that (i) the  $T_n$  and  $T_R$

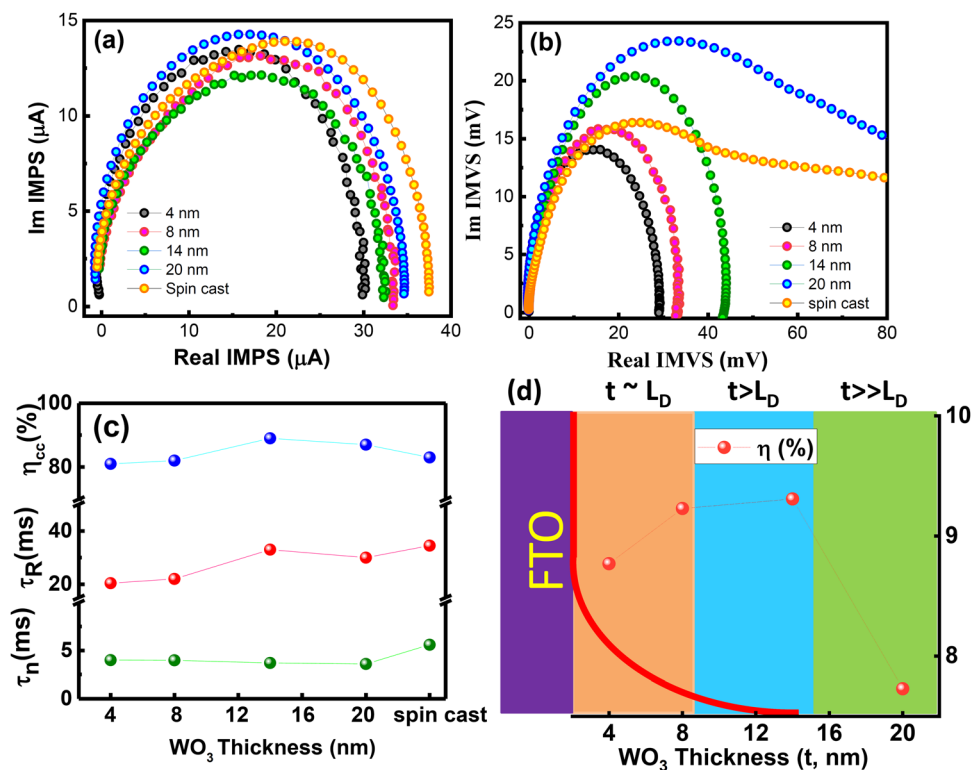


Fig. 8 (a) IMPS, (b) IMVS spectra and (c) estimated recombination time, transport time and collection efficiency as a function of  $\text{WO}_3$  BL thickness; for comparison data for DSCs fabricated with spin cast  $\text{WO}_3$  LB is also shown and (d) shows a schematic presentation of the influence of  $\text{WO}_3$  BL thickness in the Debye length regime.



remain almost constant with thickness for DSCs fabricated with  $\text{WO}_3$  BL  $\leq 8$  nm. (ii) A slight improvement in  $T_R$  and  $T_n$  is observed for DSC fabricated with BL  $\geq 14$  nm thick film and (iii) high  $T_n$  and low  $T_R$  values for DSCs employing spin cast films. These data are consistent with  $JV$  and EIS results of DSCs, which reveal higher  $J_{SC}$  and FF for DSCs based on  $\text{WO}_3$  LB as compared with that of the spin cast film. Another important parameter of the DSCs, *viz.*, electron collection efficiency can be estimated from the  $T_n$  and  $T_R$  values as follows:

$$\eta_{cc}(\%) = \left(1 - \frac{T_n}{T_R}\right) \times 100 \quad (5)$$

The  $\eta_{cc}$  of the DSCs based on 14 nm  $\text{WO}_3$  BL is much higher than that of the 20 nm thick  $\text{WO}_3$  BL and spin cast film and therefore, the best efficiency is obtained for the DSCs fabricated with 14 nm  $\text{WO}_3$  BL. Since the only difference in fabricated DSCs is the BL, this suggests that in addition to providing faster transport and reduced recombination to the photogenerated electrons, the effect of  $\text{WO}_3$  BL is manifested in the consecutive m-TiO<sub>2</sub> layers as well. The thin  $\text{WO}_3$  BL ( $\leq 14$  nm) provides the ideal surface for the deposition of the m-TiO<sub>2</sub> for device fabrication and results in fewer defects. The above findings can be presented schematically in Fig. 8(d). As shown in the figure, the Debye length of  $\text{WO}_3$  BL plays an important role in improving the device performance: DSCs fabricated with BL having thickness within  $L_D$  or near  $L_D$  perform much higher than the devices with thickness much higher than  $L_D$ .

## 4. Conclusion

In summary, we have successfully prepared ultra-thin compact BL (4–20 nm) in the range of Debye length by the LB method and studied the influence of BL thickness on DSC performance. A clear distinction in charge transport and blocking properties was observed between thin films ( $\leq 14$  nm) and thick films ( $> 20$  nm), which were related to  $L_D$ . Better interfacial properties as well as charge transport and blocking properties of DSC devices based on thin  $\text{WO}_3$  blocking layers ( $\leq 14$  nm) result in higher efficiency up to  $\sim 9.79\%$  in DSCs devices as compared to DSCs having  $\text{WO}_3$  BL of 20 nm thickness (8.02%) as well as those prepared with spin cast films (7%). This work demonstrates that employing  $\text{WO}_3$  BL of the Debye length regime results in the enhancement of the efficiency of the solar cells without compromising optical transmittance and blocking properties.

## Author contributions

N. Kumar: data curation, formal analysis. S. Choudhury: resources, validation. A. Mahajan: resources, validation. Vibha Saxena: conceptualization, data curation, formal analysis, project administration, resources, supervision, validation, visualization, writing – original draft writing – review & editing. All authors have read and agreed to the published version of the manuscript.

## Data availability

The data supporting this article have been included as part of the ESI.†

## Conflicts of interest

There are no conflicts of interest to declare.

## Acknowledgements

The authors thank Dr S. M. Yusuf, Dr L. M. Pant and Dr A. Singh for the support of this work.

## References

- 1 E. Pulli, E. Rozzi and F. Bella, Transparent photovoltaic technologies: current trends towards upscaling, *Energy Convers. Manage.*, 2020, **219**, 112982.
- 2 J.-M. Ji, H. Zhou, Y. K. Eom, C. H. Kim and H. K. Kim, 14.2% Efficiency Dye-Sensitized Solar Cells by Co-sensitizing Novel Thieno[3,2-*b*]indole-Based Organic Dyes with a Promising Porphyrin Sensitizer, *Adv. Energy Mater.*, 2020, **10**(15), 2000124.
- 3 P. Ledezma, J. Jermakka, J. Keller and S. Freguia, Impact of film thickness of ultra-thin dip-coated compact TiO<sub>2</sub> layers on the performance of mesoscopic perovskite solar cells, *Front. Microbiol.*, 2017, **8**, 750.
- 4 I. P. Liu, W.-H. Lin, C.-M. Tseng-Shan and Y.-L. Lee, Importance of Compact Blocking Layers to the Performance of Dye-Sensitized Solar Cells under Ambient Light Conditions, *ACS Appl. Mater. Interfaces*, 2018, **10**(45), 38900–38905.
- 5 W. Zhang, Y. Wu, H. W. Bahng, Y. Cao, C. Yi, Y. Saygili, J. Luo, Y. Liu, L. Kavan and J.-E. Moser, *et al.*, Comprehensive control of voltage loss enables 11.7% efficient solid-state dye-sensitized solar cells, *Energy Environ. Sci.*, 2018, **11**(7), 1779–1787, DOI: [10.1039/C8EE00661J](https://doi.org/10.1039/C8EE00661J).
- 6 M.-E. Yeoh and K.-Y. Chan, Efficiency Enhancement in Dye-Sensitized Solar Cells with ZnO and TiO<sub>2</sub> Blocking Layers, *J. Electron. Mater.*, 2019, **48**(7), 4342–4350.
- 7 M. A. Arvizu, H.-Y. Qu, U. Cindemir, Z. Qiu, E. A. Rojas-González, D. Primetzhofer, C. G. Granqvist, L. Österlund and G. A. Niklasson, Electrochromic  $\text{WO}_3$  thin films attain unprecedented durability by potentiostatic pretreatment, *J. Mater. Chem. A*, 2019, **7**(6), 2908–2918, DOI: [10.1039/C8TA09621J](https://doi.org/10.1039/C8TA09621J).
- 8 L. You, B. Liu, T. Liu, B. Fan, Y. Cai, L. Guo and Y. Sun, Organic Solar Cells Based on  $\text{WO}_{2.72}$  Nanowire Anode Buffer Layer with Enhanced Power Conversion Efficiency and Ambient Stability, *ACS Appl. Mater. Interfaces*, 2017, **9**(14), 12629–12636.
- 9 R. Shakoury, A. Arman, S. Rezaee, A. G. Korpi, S. Kulesza, C. Luna, M. Bramowicz and M. Mardani, Optical properties and morphology analysis of hexagonal  $\text{WO}_3$  thin films obtained by electron beam evaporation, *J. Mater. Sci.: Mater. Electron.*, 2021, **32**(1), 798–805.



- 10 J. M. Berak and M. J. Sienko, Effect of oxygen-deficiency on electrical transport properties of tungsten trioxide crystals, *J. Solid State Chem.*, 1970, **2**(1), 109–133.
- 11 M. Miyakawa, K. Ueda and H. Hosono, Carrier generation in highly oriented WO<sub>3</sub> films by proton or helium implantation, *J. Appl. Phys.*, 2002, **92**(4), 2017–2022.
- 12 S. S. Patil, R. M. Mane, K. V. Khot, S. S. Mali, C. Kook Hong and P. N. Bhosale, Surfactant assisted approach to development of efficient WO<sub>3</sub> photoanode for natural dye sensitized solar cell, *Sol. Energy*, 2021, **220**, 371–383.
- 13 J. Zhang, C. Shi, J. Chen, Y. Wang and M. Li, Preparation of ultra-thin and high-quality WO<sub>3</sub> compact layers and comparison of WO<sub>3</sub> and TiO<sub>2</sub> compact layer thickness in planar perovskite solar cells, *J. Solid State Chem.*, 2016, **238**, 223–228.
- 14 D. Liu, Q. Wang, C. J. Traverse, C. Yang, M. Young, P. S. Kuttipillai, S. Y. Lunt, T. W. Hamann and R. R. Lunt, Impact of Ultrathin C60 on Perovskite Photovoltaic Devices, *ACS Nano*, 2018, **12**(1), 876–883.
- 15 M. T. Masood, C. Weinberger, J. Sarfraz, E. Rosqvist, S. Sandén, O. J. Sandberg, P. Vivo, G. Hashmi, P. D. Lund and R. Österbacka, *et al.*, Impact of Film Thickness of Ultrathin Dip-Coated Compact TiO<sub>2</sub> Layers on the Performance of Mesoscopic Perovskite Solar Cells, *ACS Appl. Mater. Interfaces*, 2017, **9**(21), 17906–17913.
- 16 S. Seo, I. J. Park, M. Kim, S. Lee, C. Bae, H. S. Jung, N.-G. Park, J. Y. Kim and H. Shin, An ultra-thin, un-doped NiO hole transporting layer of highly efficient (16.4%) organic-inorganic hybrid perovskite solar cells, *Nanoscale*, 2016, **8**(22), 11403–11412, DOI: [10.1039/C6NR01601D](https://doi.org/10.1039/C6NR01601D).
- 17 J. Kukkola, M. Mohl, A.-R. Leino, J. Mäklin, N. Halonen, A. Shchukarev, Z. Konya, H. Jantunen and K. Kordas, Room temperature hydrogen sensors based on metal decorated WO<sub>3</sub> nanowires, *Sens. Actuators, B*, 2013, **186**, 90–95.
- 18 H. Cheng, Y. Liu, B. Cai, C. Hägglund, T. Kubart, G. Boschloo and H. Tian, Atomic Layer Deposition of SnO<sub>2</sub> as an Electron Transport Material for Solid-State P-type Dye-Sensitized Solar Cells, *ACS Appl. Energy Mater.*, 2022, **5**(10), 12022–12028.
- 19 Y. Li, L. Ma, Y. Yoo, G. Wang, X. Zhang and M. J. Ko, Atomic layer deposition: A versatile method to enhance TiO<sub>2</sub> nanoparticles interconnection of dye-sensitized solar cell at low temperature, *J. Ind. Eng. Chem.*, 2019, **73**, 351–356.
- 20 S. Seo, S. Jeong, H. Park, H. Shin and N.-G. Park, Atomic layer deposition for efficient and stable perovskite solar cells, *Chem. Commun.*, 2019, **55**(17), 2403–2416, DOI: [10.1039/C8CC09578G](https://doi.org/10.1039/C8CC09578G).
- 21 Y. Kuang, V. Zardetto, R. van Gils, S. Karwal, D. Koushik, M. A. Verheijen, L. E. Black, C. Weijtens, S. Veenstra and R. Andriessen, *et al.*, Low-Temperature Plasma-Assisted Atomic-Layer-Deposited SnO<sub>2</sub> as an Electron Transport Layer in Planar Perovskite Solar Cells, *ACS Appl. Mater. Interfaces*, 2018, **10**(36), 30367–30378.
- 22 S. Balasubramanyam, A. Sharma, V. Vandalon, H. C. M. Knoops, W. M. M. Kessels and A. A. Bol, Plasma-enhanced atomic layer deposition of tungsten oxide thin films using (tBuN)<sub>2</sub>(Me<sub>2</sub>N)<sub>2</sub>W and O<sub>2</sub> plasma, *J. Vac. Sci. Technol., A*, 2018, **36**(1), 01B103.
- 23 A. Jelinska, K. Bienkowski, M. Jadwiszczak, M. Pisarek, M. Strawski, D. Kurzydowski, R. Solarska and J. Augustynski, Enhanced Photocatalytic Water Splitting on Very Thin WO<sub>3</sub> Films Activated by High-Temperature Annealing, *ACS Catal.*, 2018, **8**(11), 10573–10580.
- 24 N. A. Isaac, M. Valenti, A. Schmidt-Ott and G. Biskos, Characterization of Tungsten Oxide Thin Films Produced by Spark Ablation for NO<sub>2</sub> Gas Sensing, *ACS Appl. Mater. Interfaces*, 2016, **8**(6), 3933–3939.
- 25 G. Mattoni, A. Filippetti, N. Manca, P. Zubko and A. D. Caviglia, Charge doping and large lattice expansion in oxygen-deficient heteroepitaxial WO<sub>3</sub>, *Phys. Rev. Mater.*, 2018, **2**(5), 053402.
- 26 G. Mattoni, B. de Jong, N. Manca, M. Tomellini and A. D. Caviglia, Single-Crystal Pt-Decorated WO<sub>3</sub> Ultrathin Films: A Platform for Sub-ppm Hydrogen Sensing at Room Temperature, *ACS Appl. Nano Mater.*, 2018, **1**(7), 3446–3452.
- 27 M. A. Mamun, K. Zhang, H. Baumgart and A. A. Elmustafa, Nanomechanical and Morphological Characterization of Tungsten Trioxide (WO<sub>3</sub>) Thin Films Grown by Atomic Layer Deposition, *ECS J. Solid State Sci. Technol.*, 2015, **4**(9), P398.
- 28 S. Balasubramanyam, A. Sharma, V. Vandalon, H. C. M. Knoops, W. M. M. Kessels and A. A. Bol, Plasma-enhanced atomic layer deposition of tungsten oxide thin films using (tBuN)<sub>2</sub>(Me<sub>2</sub>N)<sub>2</sub>W and O<sub>2</sub> plasma, *J. Vac. Sci. Technol., A*, 2017, **36**(1), 01B103.
- 29 O. Prakash, V. Saxena, R. K. Bedi, A. K. Debnath and A. Mahajan, Solution processable transition metal oxide ultra-thin films as alternative electron transport and hole blocking layers in dye sensitized solar cells, *J. Photochem. Photobiol., A*, 2021, **418**, 113385.
- 30 V. Saxena, N. Bhagat, S. Choudhury, A. Mahajan and A. Singh, Phase Variation of Ultrathin WO<sub>3</sub> Electron-Transport Layer Prepared by Scalable Langmuir–Blodgett Technique to Boost Efficiency of Dye Sensitized Solar Cells, *Solar RRL*, 2022, **6**(8), 2200222.
- 31 Z. Avazbaeva, W. Sung, J. Lee, M. D. Phan, K. Shin, D. Vaknin and D. Kim, Origin of the Instability of Octadecylamine Langmuir Monolayer at Low pH, *Langmuir*, 2015, **31**(51), 13753–13758.
- 32 J. T. Davies, E. K. Rideal and S. A. Rice, Interfacial Phenomena, *Phys. Today*, 1962, **15**(4), 78.
- 33 J. Li, Y. Liu, Z. Zhu, G. Zhang, T. Zou, Z. Zou, S. Zhang, D. Zeng and C. Xie, A full-sunlight-driven photocatalyst with super long-persistent energy storage ability, *Sci. Rep.*, 2013, **3**(1), 2409.
- 34 O. Prakash, V. Saxena, S. Choudhury, Tanvi, A. Singh, A. K. Debnath, A. Mahajan, K. P. Muthe and D. K. Aswal, Low temperature processable ultra-thin WO<sub>3</sub> Langmuir–Blodgett film as excellent hole blocking layer for enhanced performance in dye sensitized solar cell, *Electrochim. Acta*, 2019, **318**, 405–412.
- 35 C. V. Ramana, S. Utsunomiya, R. C. Ewing, C. M. Julien and U. Becker, Structural Stability and Phase Transitions in WO<sub>3</sub> Thin Films, *J. Phys. Chem. B*, 2006, **110**(21), 10430–10435.
- 36 Tanvi, V. Saxena, A. Singh, O. Prakash, A. Mahajan, A. K. Debnath, K. P. Muthe and S. C. Gadkari, Improved



- performance of dye sensitized solar cell via fine tuning of ultra-thin compact TiO<sub>2</sub> layer, *Sol. Energy Mater., Sol. Cells*, 2017, **170**, 127–136.
- 37 R. Memming, *Semiconductor Electrochemistry*, Wiley, 2015.
- 38 Y. Matsumoto, Y. Miura and S. Takata, Thickness-Dependent Flat Band Potential of Anatase TiO<sub>2</sub>(001) Epitaxial Films on Nb:SrTiO<sub>3</sub>(001) Investigated by UHV-Electrochemistry Approach, *J. Phys. Chem. C*, 2016, **120**(3), 1472–1477.
- 39 P. Xu, T. J. Milstein and T. E. Mallouk, Flat-Band Potentials of Molecularly Thin Metal Oxide Nanosheets, *ACS Appl. Mater. Interfaces*, 2016, **8**(18), 11539–11547.
- 40 A. Sacco, Electrochemical impedance spectroscopy: fundamentals and application in dye-sensitized solar cells, *Renewable Sustainable Energy Rev.*, 2017, **79**, 814–829.
- 41 L. Kavan, N. Tétreault, T. Moehl and M. Grätzel, Electrochemical Characterization of TiO<sub>2</sub> Blocking Layers for Dye-Sensitized Solar Cells, *J. Phys. Chem. C*, 2014, **118**(30), 16408–16418.
- 42 J. Premkumar, Development of Super-Hydrophilicity on Nitrogen-Doped TiO<sub>2</sub> Thin Film Surface by Photoelectrochemical Method under Visible Light, *Chem. Mater.*, 2004, **16**(21), 3980–3981.
- 43 S. S.-O. Youn, J. Kim, J. Na, W. Jo and G. Y. Kim, Understanding the Space-Charge Layer in SnO<sub>2</sub> for Enhanced Electron Extraction in Hybrid Perovskite Solar Cells, *ACS Appl. Mater. Interfaces*, 2022, **14**(42), 48229–48239.
- 44 F. Fabregat-Santiago, J. Bisquert, G. Garcia-Belmonte, G. Boschloo and A. Hagfeldt, Influence of electrolyte in transport and recombination in dye-sensitized solar cells studied by impedance spectroscopy, *Sol. Energy Mater. Sol. Cells*, 2005, **87**(1), 117–131.
- 45 A. Pockett, M. Spence, S. K. Thomas, D. Raptis, T. Watson and M. J. Carnie, Beyond the First Quadrant: Origin of the High Frequency Intensity-Modulated Photocurrent/Photovoltage Spectroscopy Response of Perovskite Solar Cells, *Solar RRL*, 2021, **5**(5), 2100159.

